EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	21542	(die near9 (wafer or semiconductor or substrate)) and ((insulat$4 or oxide or dielectric) near9 (wafer or semiconductor or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 12:23
L3	197081	((die or circuit) near9 (wafer or semiconductor or substrate)) and ((insulat$4 or oxide or dielectric) near9 (wafer or semiconductor or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 12:24
L4	733	((die or circuit) near9 (wafer or semiconductor or substrate)) and ((insulat$4 or oxide or dielectric) near9 (wafer or semiconductor or substrate)) and (scribe near9 die)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 12:24
L5	30	((die or circuit) near9 (wafer or semiconductor or substrate)) and ((insulat$4 or oxide or dielectric) near9 (wafer or semiconductor or substrate)) and (scribe near9 die) and ((metal or(dielectric or oxide or insulat$4)) near9 (pit or recess))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 12:26
L6	12	((die or circuit) near9 (wafer or semiconductor or substrate)) and ((insulat$4 or oxide or dielectric) near9 (wafer or semiconductor or substrate)) and (scribe near9 die) and ((metal or(dielectric or oxide or insulat$4)) near9 (pit or recess)) and ((opening or via or hole or trench) near9 (dielectric or oxide or insulat$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 12:31
L7	3	((die or circuit) near9 (wafer or semiconductor or substrate)) and ((insulat$4 or oxide or dielectric) near9 (wafer or semiconductor or substrate)) and (scribe near9 die) and ((metal or(dielectric or oxide or insulat$4)) near9 (pit or recess)) and ((opening or via or hole or trench) near9 (dielectric or oxide or insulat$4)) and stress	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 13:23

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L8	19949	stress near4 (dielectric or oxide or insulat$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 13:24
L9	162	(stress near4 (dielectric or oxide or insulat$4)) near9 fill	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 13:25
L10	85	(stress near4 (dielectric or oxide or insulat$4)) near9 fill near9 (via or hole or trench or opening)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 13:25
L11	12	(stress near4 (dielectric or oxide or insulat$4)) near9 fill near9 (via or hole or trench or opening) near9 (substrate or semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 13:26
S1	861	(wafer or semiconductor or substrate) and dielectric and (open or via or hole or trench) and scribe and die and (metal or conduct$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:02
S2	872	(wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and scribe and die and (metal or conduct$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:02
S3	414	(wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and scribe and die and (metal or conduct$4) and stress	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:02
S4	336	(wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and scribe and die and (metal or conduct$4) and stress and plurality	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:02

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S5	272	(wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and scribe and die and (metal or conduct$4) and stress and plurality and expos$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:03
S6	206	(wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and scribe and die and (metal or conduct$4) and stress and plurality and expos$3 and region	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:03
S7	27	(wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and scribe and die and (metal or conduct$4) and stress and plurality and expos$3 and region and pit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:19
S8	6	die and "scribe line" and (wafer or semicondcutor or substrate) and dielectric and (opening or via or hole or trench) and (metal or conduct$4) and pit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:24
S9	43	(wafer or semicondcutor or substrate) and dielectric and (opening or via or hole or trench) and (metal or conduct$4) and pit and "scribe line"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:02
S10	6	(wafer or semicondcutor or substrate) and dielectric and (opening or via or hole or trench) and (metal or conduct$4) and pit and "scribe line" and die	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 12:59
S11	194	((wafer or semiconductor or substrate) near4 die) and (dielectric or oxide or insulat$4) and (via or hole or trench) and (copper or tungsten) and (metal or polysilicon) and groove and photolithograph$8 and etch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:05

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S12	20	((wafer or semiconductor or substrate) near4 die) and (dielectric or oxide or insulat$4) and (via or hole or trench or open$3) and (copper or tungsten) and (metal or polysilicon) and groove and photolithograph$8 and etch and (scribe near4 line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:06
S13	0	((wafer or semiconductor or substrate) near4 die) and (dielectric or oxide or insulat$4) and (via or hole or trench or open$3) and (copper or tungsten) and (metal or polysilicon) and groove and photolithograph$8 and etch and (scribe near4 line) and pit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:13
S14	27	((wafer or semiconductor or substrate) near4 die) and (dielectric or oxide or insulat$4) and (via or hole or trench or open$3) and (copper or tungsten) and (metal or polysilicon) and groove and photolithograph$8 and etch and pit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:15
S15	15	((wafer or semiconductor or substrate) near4 die) and (dielectric or oxide or insulat$4) and (via or hole or trench or open$3) and (copper or tungsten) and (metal or polysilicon) and groove and photolithograph$8 and etch and pit and stress	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 07:19
S16	33326	(stress near4 (wafer or semiconductor or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:17
S17	787	((stress near4 (wafer or semiconductor or substrate)) near4 die)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:17

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S18	480	(die near8 (wafer or semiconductor or substrate)) and (dielectric or oxide or insulat$4) and (open$3 or via or hole or trench or groove) and pit$2 and (photolithographic$4 or etch$4) and plug and (metal or conduct$4 or polysilicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 07:24
S19	70	(die near8 (wafer or semiconductor or substrate)) and (dielectric or oxide or insulat$4) and (open$3 or via or hole or trench or groove) and pit$2 and (photolithographic$4 or etch$4) and plug and (metal or conduct$4 or polysilicon) and (scribe near line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 07:25
S20	63	(die near8 (wafer or semiconductor or substrate)) and (dielectric or oxide or insulat$4) and (open$3 or via or hole or trench or groove) and pit$2 and (photolithographic$4 or etch$4) and plug and (metal or conduct$4 or polysilicon) and (scribe near line) and (tungsten or copper)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 12:22